

NPN BDX42 – BDX43– BDX44

SILICON PLANAR DARLINGTON TRANSISTORS

The BDX42, BDX43 and BDX44 are silicon NPN planar Darlington transistors and are mounted in Jedec TO-126 plastic package.

They are intented for use in industrial switching applications.

The complementary PNP types are the BDX45, BDX46 and BDX47 respectively. Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit	
			BDX42	60	
V _{CBO}	5		BDX43	80	V
			BDX44	90	l
			BDX42	45	
V _{CER}	5		BDX43	60	V
			BDX44	80	
V _{EBO}	Emitter-Base Voltage			5	V
I _C	Collector Current	lc		1	
	Collector Current	I _{CM}		2	A
I _B	Base Current	·		0.1	А
Ρ _τ	Power Dissipation $@ T_c = 25^\circ$		1.25	Watts	
TJ	Junction Temperature		150	°C	
Ts	Storage Temperature			-65 to +150	

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit	
R _{thJ-a}	Thermal Resistance, Junction to Ambient	100	K/W	
R _{thJ-mb}	Thermal Resistance, Junction to Mounting base	10	1.7.4.4	



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ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition	l(s)	Min	Тур	Max	Unit
		$V_{BE} = 0$; $V_{CE} = 45V$	BDX42	-	-	10	
I _{CES}	Collector cut-off current	$V_{BE} = 0$; $V_{CE} = 60V$	BDX43	-	-	10	μA
		$V_{BE} = 0$; $V_{CE} = 80V$	BDX44	-	-	10	
	Emitter cut-off current	$I_{\rm C} = 0$; $V_{\rm EB} = 4V$	BDX42	-	-	10	μΑ
I _{EBO}			BDX43	-	-	10	
			BDX44	-	-	10	
			BDX42	-	-	1.3	
		I_{C} =500 m A, I_{B} =0.5 mA	BDX43	-	-	1.3	
			BDX44	-	-	1.3	
		I _C =1.0 A, I _B =1.0 mA	BDX43	-	-	1.6	
			BDX42	-	-	1.6	
	Collector-Emitter	I _C =1.0 A, I _B =4.0 mA	BDX44	-	-	1.6	
$V_{CE(SAT)}$	saturation Voltage (*)	1 - 500 = 0.1 = 0.5 = 0.0	BDX42	-	-	1.3	V
	Saturation Voltage ()	$I_{C}=500 \text{ m A}, I_{B}=0.5 \text{ mA}$	BDX43	-	-	1.3	
		Tj=150 °C	BDX44	-	-	1.3	
		I _C =1.0 A, I _B =1.0 mA Tj=150 °C	BDX43	-	-	1.8	
		I _C =1.0 A, I _B =4.0 mA Tj=150 °C	BDX42	-	-	1.6	
			BDX44	-	-	1.6	
	Base-Emitter saturation Voltage (*)	I _C =500 m A, I _B =0.5 mA	BDX42	-	-	1.9	V
			BDX43	-	-	1.9	
V			BDX44	-	-	1.9	
$V_{BE(SAT)}$		I _C =1.0 A, I _B =1.0 mA	BDX43	-	-	2.2	
		I _C =1.0 A, I _B =4.0 mA	BDX42	-	-	2.2	
			BDX44	-	-	2.2	
			BDX42	1000	-	-	
		V _{CE} =10 V, I _C =150 mA	BDX43	1000	-	-	
b	DC Current Coin		BDX44	1000	-	-	
h _{FE}	DC Current Gain		BDX42	2000	-	-	
		V_{CE} =10 V, I _C =500 mA	BDX43	2000	-	-	
			BDX44	2000	-	-	
h _{fe}	Small Signal Current Gain	$V_{CE}=5.0 \text{ V}, \text{ I}_{C}=500 \text{ mA}$	BDX42	-	10	-	
			BDX43	-	10	-	
			BDX44	-	10	-	
t _{on}	Turn-on time	I _c =500 mA		-	400	-	
t _{off}	Turn-off time	I _{Bon} = -I _{Boff} =0.5 mA		-	1500	-	ns
t _{on}	Turn-on time	I _C =1 A - 400		-			
t _{off}	Turn-off time	I _{Bon} = -I _{Boff} =1.0 mA		_	1500	-	ns

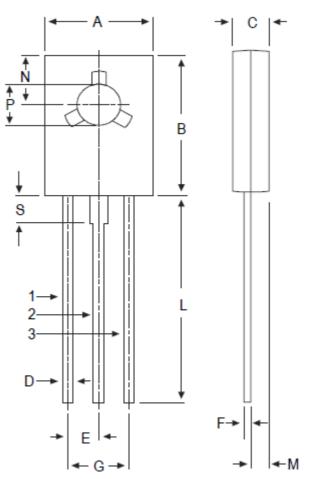


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MECHANICAL DATA CASE TO-126

	DIMENSIONS		
	min	max	
А	7.4	7.8	
В	10.5	10.8	
С	2.4	2.7	
D	0.7	0.9	
E	2.25 typ.		
F	0.49	0.75	
G	4.4 typ.		
L	15.7 typ.		
М	1.27 typ.		
N	3.75 typ.		
Р	3.0	3.2	
S	2.54 typ.		

Pin 1 :	Emitter
Pin 2 :	Collector
Pin 3 :	Base



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